

SiC Development Engineer

Location: Korea (Bucheon)

Department: CRD (Corporate R&D)

Description

- Simulation works for verifying the new SiC technology and predicting the device electrical characteristics.
- Analyze SiC technology and trends.
- Creating new SiC device concepts and realizing next generation SiC technologies.
- SiC derivative technology development from the proven new technology.
- DOE planning to implement the new idea into the experiment and do the evaluation and analysis.
- Cost and yield analysis for the new SiC technologies.
- Cost saving works including yield-up activities for the new SiC technologies.
- Technical support for issues in production

Qualifications

- Above BS degree or over in Semiconductor device physics or technology, Microelectronics or equivalent.
- 5-8 years of experience in power semiconductor design and/or fabrication.
- Hand-on experience in power semiconductors design and technology development.
- Proficiency in TCAD simulation (Synopsys simulator preferred)
- Understanding of material and strong knowledge in device physics, fabrication and characterization principles
- Knowledge and experience in design for reliability and robustness.
- Ability to address design and engineering issues and to provide proper solution.
- Strong communication skills in English